

MITSUBISHI IGBT MODULES  
**CM200RL-12NF**

HIGH POWER SWITCHING USE

**CM200RL-12NF**



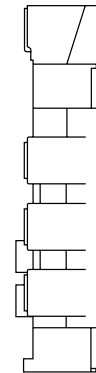
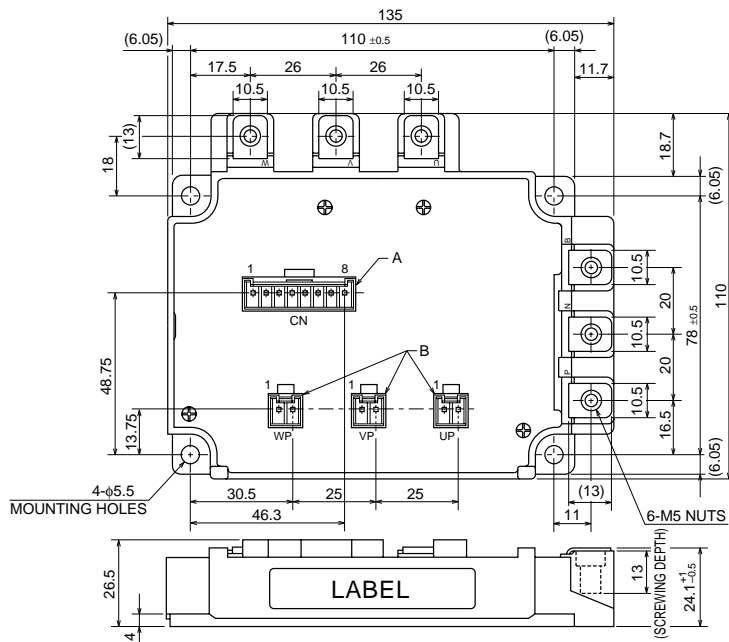
- IC .....200A
- VCES .....600V
- Insulated Type
- 7-elements in a pack

**APPLICATION**

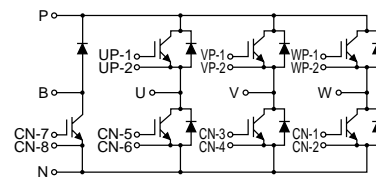
AC drive inverters & Servo controls, etc

**OUTLINE DRAWING & CIRCUIT DIAGRAM**

Dimensions in mm



Housing Type of A and B  
 (J.S.T.Mfg.Co.Ltd)  
 A = B8P-VH-FB-B, B = B2P-VH-FB-B



CIRCUIT DIAGRAM

## CM200RL-12NF

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**ABSOLUTE MAXIMUM RATINGS (T<sub>j</sub> = 25°C)**  
**INVERTER PART**

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CES</sub>	Collector-emitter voltage	G-E Short	600	V
V <sub>GES</sub>	Gate-emitter voltage	C-E Short	±20	V
I <sub>C</sub>	Collector current	DC, T <sub>C</sub> = 88°C*1	200	A
I <sub>CM</sub>		Pulse (Note 2)	400	A
I <sub>E</sub> (Note 1)	Emitter current		200	A
I <sub>EM</sub> (Note 1)		Pulse (Note 2)	400	A
P <sub>C</sub> (Note 3)	Maximum collector dissipation	T <sub>C</sub> = 25°C	890	W

**BRAKE PART**

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CES</sub>	Collector-emitter voltage	G-E Short	600	V
V <sub>GES</sub>	Gate-emitter voltage	C-E Short	±20	V
I <sub>C</sub>	Collector current	DC, T <sub>C</sub> = 99°C*1	100	A
I <sub>CM</sub>		Pulse (Note 2)	200	A
P <sub>C</sub> (Note 3)	Maximum collector dissipation	T <sub>C</sub> = 25°C	540	W
V <sub>RRM</sub>	Repetitive peak reverse voltage	Clamp diode part	600	V
I <sub>FM</sub>	Forward current	Clamp diode part	100	A

**(COMMON RATING)**

Symbol	Parameter	Conditions	Ratings	Unit
T <sub>j</sub>	Junction temperature		-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-40 ~ +125	°C
V <sub>iso</sub>	Isolation voltage	Main Terminal to base plate, AC 1 min.	2500	V
—	Torque strength	Main Terminal M5	2.5 ~ 3.5	N • m
—		Mounting holes M5	2.5 ~ 3.5	N • m
—	Weight	Typical value	750	g

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HIGH POWER SWITCHING USE

## ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25°C) INVERTER PART

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA
VGE(th)	Gate-emitter threshold voltage	IC = 20mA, VCE = 10V	6	7	8	V
IGES	Gate leakage current	VGE = VGES, VCE = 0V	—	—	0.5	μA
VCE(sat)	Collector-emitter saturation voltage	IC = 200A, VGE = 15V	—	1.7	2.2	V
		T <sub>j</sub> = 125°C	—	1.7	—	
Cies	Input capacitance	VCE = 10V VGE = 0V	—	—	30	nF
Coēs	Output capacitance		—	—	3.7	nF
Cres	Reverse transfer capacitance		—	—	1.2	nF
QG	Total gate charge	VCC = 300V, IC = 200A, VGE = 15V	—	800	—	nC
td(on)	Turn-on delay time	VCC = 300V, IC = 200A VGE1 = VGE2 = 15V RG = 3.1Ω, Inductive load switching operation IE = 200A	—	—	120	ns
tr	Turn-on rise time		—	—	100	ns
td(off)	Turn-off delay time		—	—	300	ns
tf	Turn-off fall time		—	—	300	ns
t <sub>rr</sub> (Note 1)	Reverse recovery time		—	—	150	ns
Q <sub>rr</sub> (Note 1)	Reverse recovery charge		—	4.8	—	μC
VEC(Note 1)	Emitter-collector voltage	IE = 200A, VGE = 0V	—	—	2.8	V
R <sub>th(j-c)Q</sub>	Thermal resistance	IGBT part (1/6 module) <sup>*1</sup>	—	—	0.14	°C/W
R <sub>th(j-c)R</sub>		FWDi part (1/6 module) <sup>*1</sup>	—	—	0.22	°C/W
R <sub>th(c-f)</sub>	Contact thermal resistance	Case to fin, Thermal compound Applied (1/6 module) <sup>*2</sup>	—	0.051	—	°C/W
RG	External gate resistance		3.1	—	31	Ω

## BRAKE PART

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA
VGE(th)	Gate-emitter threshold voltage	IC = 10mA	6	7	8	V
IGES	Gate leakage current	VGE = VGES, VCE = 0V	—	—	0.5	μA
VCE(sat)	Collector-emitter saturation voltage	IC = 100A, VGE = 15V	—	1.7	2.2	V
		T <sub>j</sub> = 125°C	—	1.7	—	
Cies	Input capacitance	VCE = 10V VGE = 0V	—	—	15	nF
Coēs	Output capacitance		—	—	1.9	nF
Cres	Reverse transfer capacitance		—	—	0.6	nF
QG	Total gate charge	VCC = 300V, IC = 100A, VGE = 15V	—	400	—	nC
VFM	Forward voltage drop	IF = 100A	—	—	2.8	V
R <sub>th(j-c)Q</sub>	Thermal resistance	IGBT part <sup>*1</sup>	—	—	0.23	°C/W
R <sub>th(j-c)R</sub>		Clamp diode part <sup>*1</sup>	—	—	0.41	°C/W
RG	External gate resistance		6.3	—	63	Ω

\*1 : T<sub>c</sub> measured point is just under the chips.

If you use this value, R<sub>th(f-a)</sub> should be measured just under the chips.

\*2 : Typical value is measured by using Shin-etsu Silicone "G-746".

Note 1. IE, VEC, t<sub>rr</sub> & Q<sub>rr</sub> represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temp. (T<sub>j</sub>) does not exceed T<sub>jmax</sub> rating.

3. Junction temperature (T<sub>j</sub>) should not increase beyond 150°C.

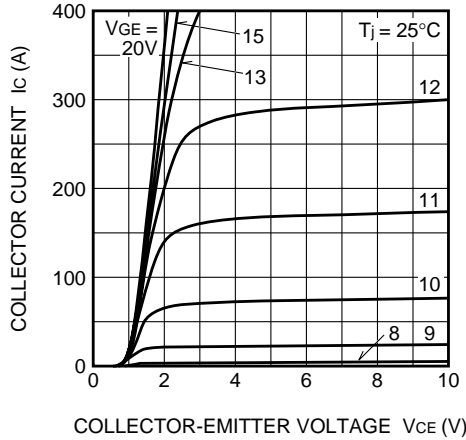
4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

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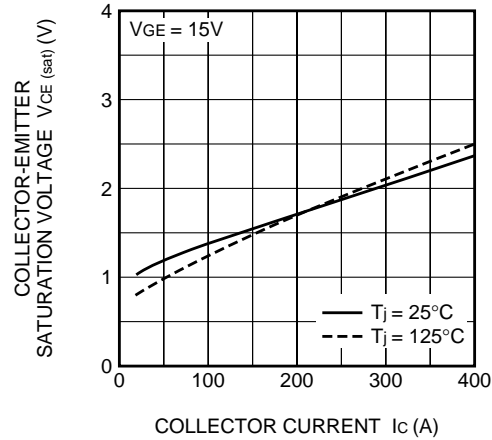
HIGH POWER SWITCHING USE

## PERFORMANCE CURVES

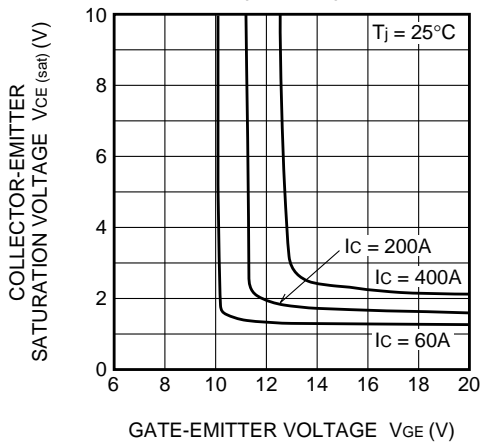
**OUTPUT CHARACTERISTICS (TYPICAL)**



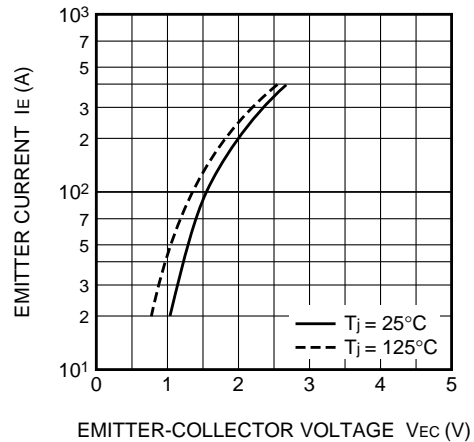
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



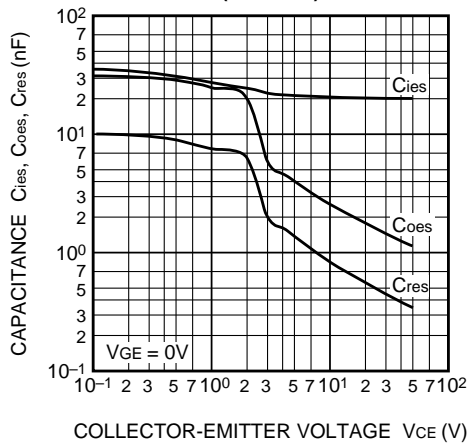
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



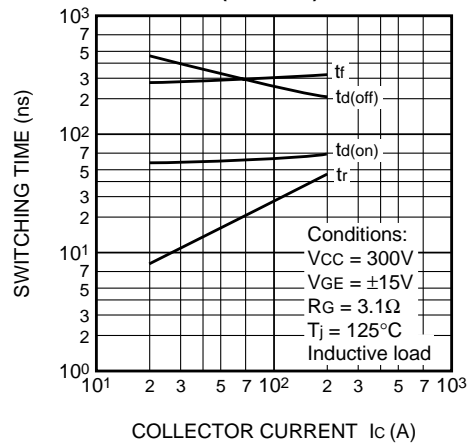
**FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)**



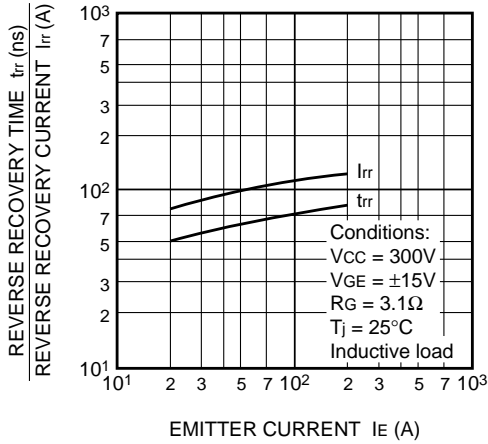
**CAPACITANCE-VCE CHARACTERISTICS (TYPICAL)**



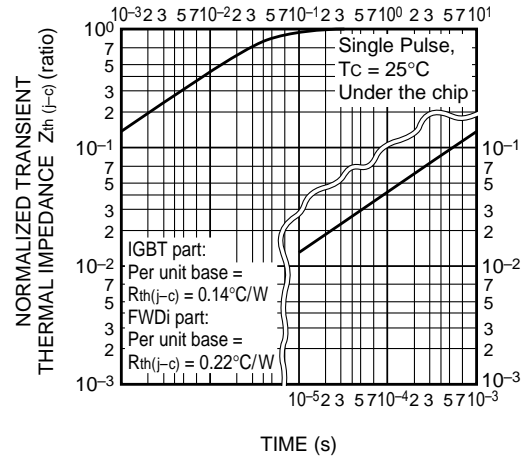
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**



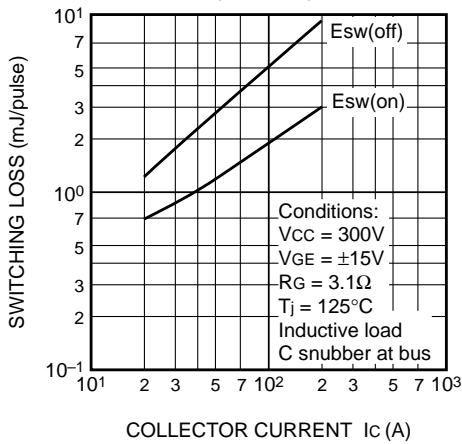
REVERSE RECOVERY CHARACTERISTICS OF FREE-WHEEL DIODE (TYPICAL)



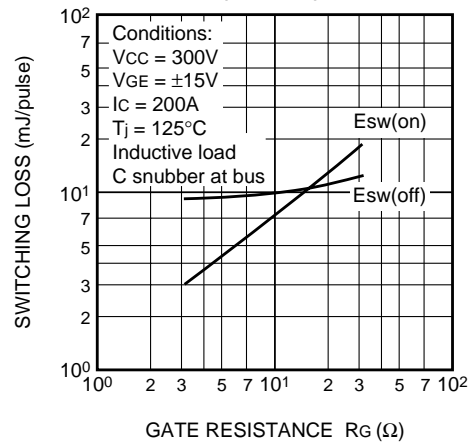
TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT part & FWDi part)



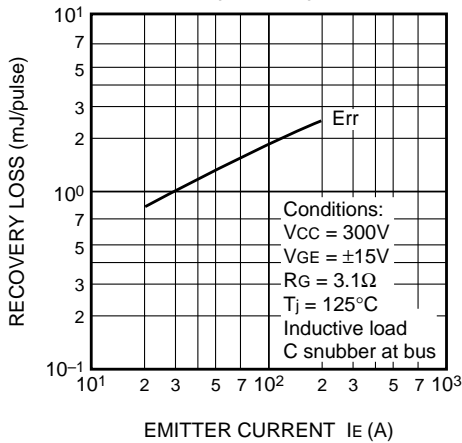
SWITCHING LOSS vs. COLLECTOR CURRENT (TYPICAL)



SWITCHING LOSS vs. GATE RESISTANCE (TYPICAL)



RECOVERY LOSS vs.  $I_E$  (TYPICAL)



RECOVERY LOSS vs. GATE RESISTANCE (TYPICAL)

